IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in this application:

1-8. (Canceled)

9. (Currently Amended) A method of repairing a light emitting device comprising:

applying a first reverse bias voltage between an anode and a cathode of the light emitting device; and

applying a second reverse bias voltage between the anode and the cathode of the light emitting device after applying the first reverse bias voltage,

wherein the anode and the cathode are located in a light emitting element with a light emitting layer interposed therebetween, ~~and~~

wherein the first reverse bias voltage and the second reverse bias voltage are selected between zero volt and an avalanche voltage, and

wherein magnitude of the second reverse bias voltage is ~~higher~~ lower than magnitude of the first reverse bias voltage.

10. (Previously presented) A method according to claim 9, wherein the first reverse bias voltage and the second reverse bias voltage are within ± 15% of an avalanche voltage of the light emitting element.

11. (Original) A method according to claim 9, wherein the light emitting element is an electroluminescence element.

12-16. (Canceled)

17. (Currently Amended) A method of repairing a light emitting device comprising:

applying a first reverse bias voltage between an anode and a cathode of the light emitting device; and

applying a second reverse bias voltage between the anode and the cathode of the light emitting device after applying the first reverse bias voltage, thereby making a portion where a reverse bias current flows between the anode and the cathode insulative,

wherein the anode and the cathode are located in a light emitting element with a light emitting layer interposed therebetween, ~~and~~

wherein the first reverse bias voltage and the second reverse bias voltage are selected between zero volt and an avalanche voltage, and

wherein magnitude of the second reverse bias voltage is ~~higher~~ lower than magnitude of the first reverse bias voltage.

18. (Previously presented) A method according to claim 17, wherein the first reverse bias voltage and the second reverse bias voltage are within ± 15% of an avalanche voltage of the light emitting element.

19. (Original) A method according to claim 17, wherein the light emitting element is an electroluminescence element.

20-32. (Canceled)

33. (Currently Amended) A method of repairing a light emitting device comprising:

applying a first reverse bias voltage between an anode and a cathode of the light emitting device; and

applying a second reverse bias voltage between the anode and the cathode of the light emitting device after applying the first reverse bias voltage, thereby making a portion where a reverse bias current flows between the anode and the cathode highly resistive,

wherein the anode and the cathode are located in a light emitting element with a light emitting layer interposed therebetween, ~~and~~

wherein the first reverse bias voltage and the second reverse bias voltage are selected between zero volt and an avalanche voltage, and

wherein magnitude of the second reverse bias voltage is ~~higher~~ lower than magnitude of the first reverse bias voltage.

34. (Previously presented) A method according to claim 33, wherein the first reverse bias voltage and the second reverse bias voltage are within ± 15% of an avalanche voltage of the light emitting element.

35. (Original) A method according to claim 33, wherein the light emitting element is an electroluminescence element.

36-58. (Canceled)

59. (Previously Presented) A method according to claim 9, wherein the light emitting layer comprises a defect portion.

60. (Previously Presented) A method according to claim 17, wherein the light emitting layer comprises a defect portion.

61. (Previously Presented) A method according to claim 33, wherein the light emitting layer comprises a defect portion.

62. (Canceled)

63. (Canceled)

64. (Currently Amended) A method of repairing a light emitting device comprising:

applying a first reverse bias voltage between an anode and a cathode of the light emitting device; and

applying a second reverse bias voltage between the anode and the cathode of the light emitting device after applying the first reverse bias voltage,

wherein the anode and the cathode are located in a light emitting element with a light emitting layer interposed therebetween,

wherein the first reverse bias voltage and the second reverse bias voltage are selected between zero volt and an avalanche voltage,

wherein magnitude of the second reverse bias voltage is ~~higher~~ lower than magnitude of the first reverse bias voltage, and

wherein the first reverse bias voltage and the second reverse bias voltage are rectangular waves.

65. (Previously presented) A method according to claim 64, wherein the first reverse bias voltage and the second reverse bias voltage are within ± 15% of an avalanche voltage of the light emitting element.

66. (Previously presented) A method according to claim 64, wherein the light emitting element is an electroluminescence element.

67. (Previously presented) A method according to claim 64, wherein the light emitting layer comprises a defect portion.

68. (Currently Amended) A method of repairing a light emitting device comprising:

applying a first reverse bias voltage between an anode and a cathode of the light emitting device; and

applying a second reverse bias voltage between the anode and the cathode of the light emitting device after applying the first reverse bias voltage, thereby making a portion where a reverse bias current flows between the anode and the cathode insulative,

wherein the anode and the cathode are located in a light emitting element with a light emitting layer interposed therebetween,

wherein the first reverse bias voltage and the second reverse bias voltage are selected between zero volt and an avalanche voltage,

wherein magnitude of the second reverse bias voltage is ~~higher~~ lower than magnitude of the first reverse bias voltage, and

wherein the first reverse bias voltage and the second reverse bias voltage are rectangular waves.

69. (Previously presented) A method according to claim 68, wherein the first reverse bias voltage and the second reverse bias voltage are within ± 15% of an avalanche voltage of the light emitting element.

70. (Previously presented) A method according to claim 68, wherein the light emitting element is an electroluminescence element.

71. (Previously presented) A method according to claim 68, wherein the light emitting layer comprises a defect portion.

72. (Currently Amended) A method of repairing a light emitting device comprising:

applying a first reverse bias voltage between an anode and a cathode of the light emitting device; and

applying a second reverse bias voltage between the anode and the cathode of the light emitting device after applying the first reverse bias voltage, thereby making a portion where a reverse bias current flows between the anode and the cathode highly resistive,

wherein the anode and the cathode are located in a light emitting element with a light emitting layer interposed therebetween,

wherein the first reverse bias voltage and the second reverse bias voltage are selected between zero volt and an avalanche voltage,

wherein magnitude of the second reverse bias voltage is ~~higher~~ lower than magnitude of the first reverse bias voltage, and

wherein the first reverse bias voltage and the second reverse bias voltage are rectangular waves.

73.(Previously presented) A method according to claim 72, wherein the first reverse bias voltage and the second reverse bias voltage are within ± 15% of an avalanche voltage of the light emitting element.

74.(Previously presented) A method according to claim 72, wherein the light emitting element is an electroluminescence element.

75.(Previously presented) A method according to claim 72, wherein the light emitting layer comprises a defect portion.

76. (New) A method of repairing a light emitting device comprising:

applying a first reverse bias voltage between an anode and a cathode of the light emitting device; and

applying a second reverse bias voltage between the anode and the cathode of the light emitting device after applying the first reverse bias voltage,

wherein the anode and the cathode are located in a light emitting element with a light emitting layer interposed therebetween,

wherein the first reverse bias voltage and the second reverse bias voltage are lower than zero volt, and

wherein magnitude of the second reverse bias voltage is lower than magnitude of the first reverse bias voltage.

77. (New) A method according to claim 76, wherein the first reverse bias voltage and the second reverse bias voltage are within ± 15% of an avalanche voltage of the light emitting element.

78. (New) A method according to claim 76, wherein the light emitting element is an electroluminescence element.